

SURFACE MOUNT DUAL PNP SILICON TRANSISTORS



Central semiconductor Corp.

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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLT2907A consists of two individual, isolated 2907A PNP silicon transistors, manufactured by the epitaxial planar process and epoxy molded in an SOT-563 surface mount package. This PICOmini[™] devices has been designed for small signal general purpose and switching applications.

MARKING CODE: L07

MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	۱ _C	600	mA
Power Dissipation	PD	350	mW
Operating and Storage Junction Temperature	TJ, T _{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
ICBO	V _{CB} =50V		10	nA
ICBO	V _{CB} =50V, T _A =125°C		10	μA
ICEV	V _{CE} =30V, V _{BE} =0.5V		50	nA
BVCBO	Ι _C =10μΑ	60		V
BV _{CEO}	I _C =10mA	60		V
BVEBO	Ι _Ε =10μΑ	5.0		V
V _{CE(SAT)}	I _C =150mA, I _B =15mA		0.4	V
V _{CE} (SAT)	I _C =500mA, I _B =50mA		1.6	V
V _{BE(SAT)}	I _C =150mA, I _B =15mA		1.3	V
V _{BE(SAT)}	I _C =500mA, I _B =50mA		2.6	V
h _{FE}	V _{CE} =10V, I _C =0.1mA	75		
h _{FE}	V _{CE} =10V, I _C =1.0mA	100		
h _{FE}	V _{CE} =10V, I _C =10mA	100		
h _{FE}	V _{CE} =10V, I _C =150mA	100	300	
hFE	V _{CE} =10V, I _C =500mA	50		

R2 (20-January 2010)



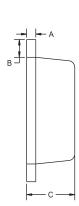
CMLT2907A

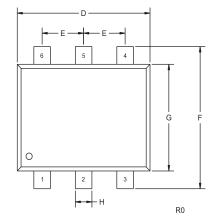
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ELECTRICAL CHARACTERISTICS - Continued:

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f _T	V _{CE} =20V, I _C =50mA, f=100MHz	200		MHz
Cob	V _{CB} =10V, I _E =0, f=1.0MHz		8.0	pF
C _{ib}	V _{BE} =2.0V, I _C =0, f=1.0MHz		30	pF
t _{on}	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA		45	ns
^t d	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA		10	ns
t _r	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA		40	ns
t _{off}	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		100	ns
t _s	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		80	ns
t _f	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		30	ns

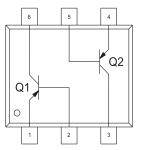
SOT-563 CASE - MECHANICAL OUTLINE





DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
А	0.004	0.007	0.10	0.18
В	0.008		0.20	
С	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
Н	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)



LEAD CODE:

1) Emitter Q1

- 2) Base Q1 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

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